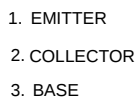
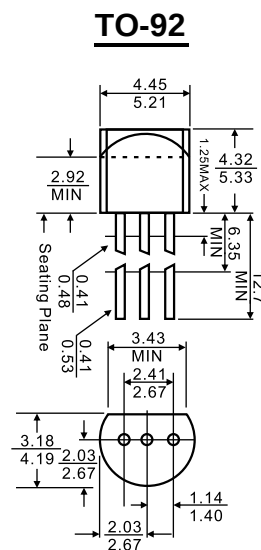


TO-92 Bipolar Transistors



✧ **Collector output capacitance :**
Cob=11 pF (TYP),20 pF (MAX)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	70	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	500	mA
P_C	Collector Power Dissipation	750	mW
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55-150	°C



Dimensions in inches and (millimeters)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10\mu A, I_E = 0$	80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 2mA, I_B = 0$	70			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB} = 20V, I_E = 0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 10V, I_C = 150mA$	85		340	
	$h_{FE(2)}$	$V_{CE} = 10V, I_C = 500mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 300mA, I_B = 30mA$			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 300mA, I_B = 30mA$			1.5	V
Transition frequency	f_T	$V_{CE} = 10V, I_C = 50mA, f = 200MHz$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$		11	20	pF

Rank	Q	R	S
Range	85-170	120-240	170-340

2SC1318(NPN)

TO-92 Bipolar Transistors

Typical Characteristics

